

NPN 14 GHz wideband transistor

Rev. 2 — 15 September 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343R plastic package.

### 1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

### **1.3 Applications**

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
  - analog and digital cellular telephones
  - cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
  - radar detectors
  - pagers
  - Satellite Antenna TeleVision (SATV) tuners

### 1.4 Quick reference data

#### Table 1.Quick reference data

Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-		-	15	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-		-	6	V
I <sub>C</sub>	collector current (DC)		-		-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145 \ ^{\circ}C$	<u>[1]</u> -		-	60	mW
h <sub>FE</sub>	DC current gain	$\begin{array}{l} I_{C} = 5 \text{ mA};  V_{CE} = 3  \text{V}; \\ T_{j} = 25 \ ^{\circ}\text{C} \end{array}$	6	0	100	200	
C <sub>CBS</sub>	collector-base capacitance	$V_{CB} = 5 V$ ; f = 1 MHz; emitter grounded	-		0.17	0.3	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 5 mA; V <sub>CE</sub> = 3 V; f = 1 GHz; T <sub>amb</sub> = 25 °C	-		14	-	GHz



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Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
MSG	maximum stable gain	I <sub>C</sub> = 5 mA; V <sub>CE</sub> = 3 V; f = 1.8 GHz; T <sub>amb</sub> = 25 °C	-	18	-	dB
S <sub>21</sub>   <sup>2</sup>	insertion power gain	$ \begin{split} & {\sf I}_{\sf C} = 5 \; {\sf mA}; \; {\sf V}_{\sf CE} = 3 \; {\sf V}; \\ & {\sf f} = 1.8 \; {\sf GHz}; \; {\sf T}_{\sf amb} = 25 \; {}^{\circ}{\sf C}; \\ & {\sf Z}_{\sf S} = {\sf Z}_{\sf L} = 50 \; \Omega \end{split} $	-	14	-	dB
NF	noise figure	$\Gamma_{s} = \Gamma_{opt}; I_{C} = 1 \text{ mA};$ V <sub>CE</sub> = 3 V; f = 2 GHz	-	1	-	dB

#### Table 4 . . . .

[1]  $T_{sp}$  is the temperature at the soldering point of the collector pin.

#### **Pinning information** 2.

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	collector		
2	emitter		1
3	base		3
4	emitter		2, 4 sym086

#### **Ordering information** 3.

Table 3. Ordering information			
Type number	Package		
	Name	Description	Version
BFG310W/XR	-	plastic surface mounted package; reverse pinning; 4 leads	SOT343R

### 4. Marking

Table 4.	Marking codes	
Type number	er	Marking code <sup>[1]</sup>
BFG310W/X	(R	A7*

[1] \* = p: made in Hong Kong.

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### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	15	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	6	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	2	V
I <sub>C</sub>	collector current (DC)		-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145 \ ^{\circ}C$	<u>[1]</u> -	60	mW
T <sub>stg</sub>	storage temperature		-65	+175	°C
Tj	junction temperature		-	175	°C

[1]  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 6. Thermal characteristics

### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	$T_{sp} \le 145 \ ^{\circ}C$	<u>[1]</u> 530	K/W

[1]  $T_{sp}$  is the temperature at the soldering point of the collector pin.

### 7. Characteristics

#### Table 7.Characteristics

 $T_i = 25 \ ^{\circ}C$ ; unless otherwise specified.

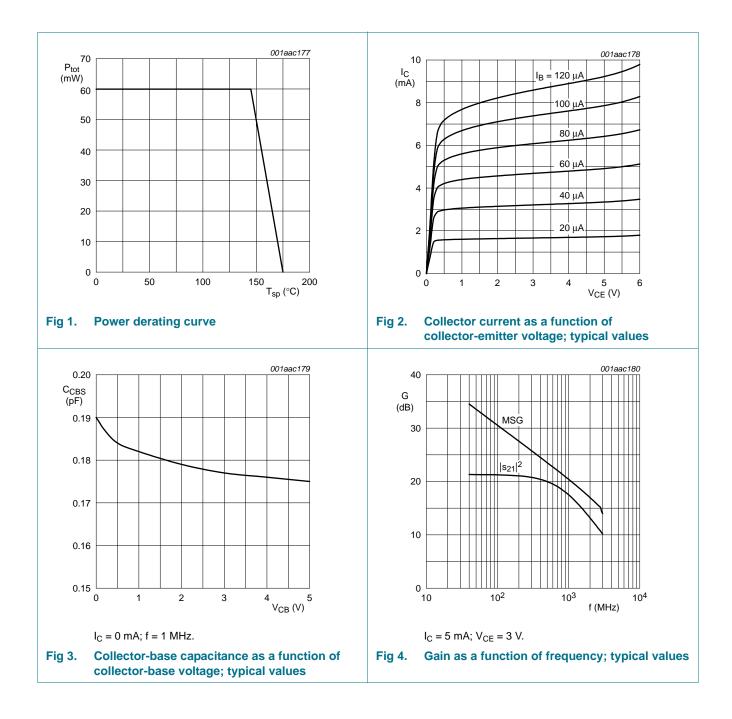
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$I_{E} = 0 \text{ A}; V_{CB} = 6 \text{ V}$	-	-	15	nA
h <sub>FE</sub>	DC current gain	$I_{C} = 5 \text{ mA}; V_{CE} = 3 \text{ V}$	60	100	200	
C <sub>CBS</sub>	collector-base capacitance	$V_{CB}$ = 5 V; f = 1 MHz; emitter grounded	-	0.17	0.3	pF
C <sub>CES</sub>	collector-emitter capacitance	$V_{CE}$ = 5 V; f = 1 MHz; base grounded	-	0.22	-	pF
C <sub>EBS</sub>	emitter-base capacitance	$V_{EB}$ = 0.5 V; f = 1 MHz; collector grounded	-	0.16	-	pF
f <sub>T</sub>	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	14	-	GHz
MSG	maximum stable gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; \text{ f} = 1.8 \text{ GHz};$ $T_{amb} = 25 \text{ °C}$	-	18	-	dB
$ s_{21} ^2$	insertion power gain	$\label{eq:IC} \begin{array}{l} I_C = 5 \text{ mA};  V_{CE} = 3  V;  T_{amb} = 25 ^\circ \text{C}; \\ Z_S = Z_L = 50  \Omega \end{array}$				
		f = 1.8 GHz	-	14	-	dB
		f = 3 GHz	-	11	-	dB
NF	noise figure	$\Gamma_{s} = \Gamma_{opt}$ ; I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 3 V; f = 2 GHz	-	1	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	$I_C$ = 5 mA; V <sub>CE</sub> = 3 V; f = 1.8 GHz; T <sub>amb</sub> = 25 °C; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω	-	1.8	-	dBm
IP3	third order intercept point	$I_{C}$ = 5 mA; V <sub>CE</sub> = 3 V; f = 1.8 GHz; T <sub>amb</sub> = 25 °C; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω	-	8.5	-	dBm

BFG310W\_XR

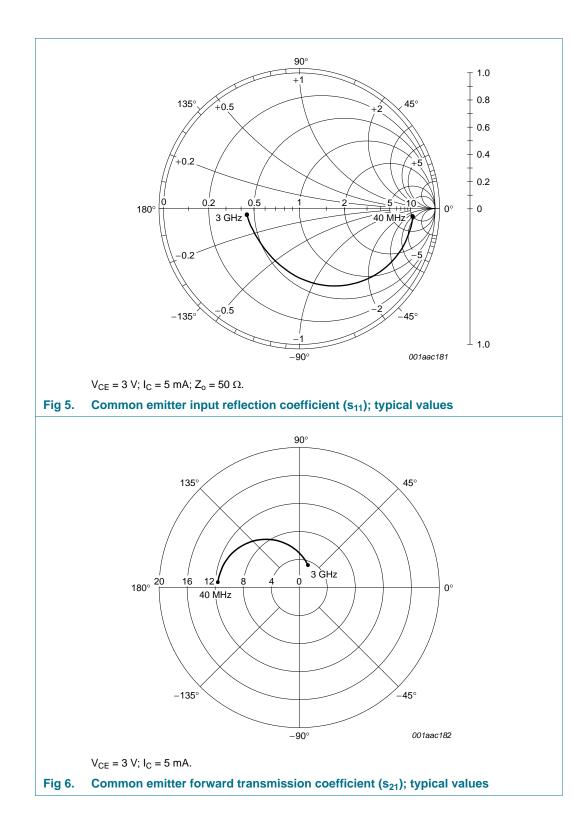
### **NXP Semiconductors**

## BFG310W/XR

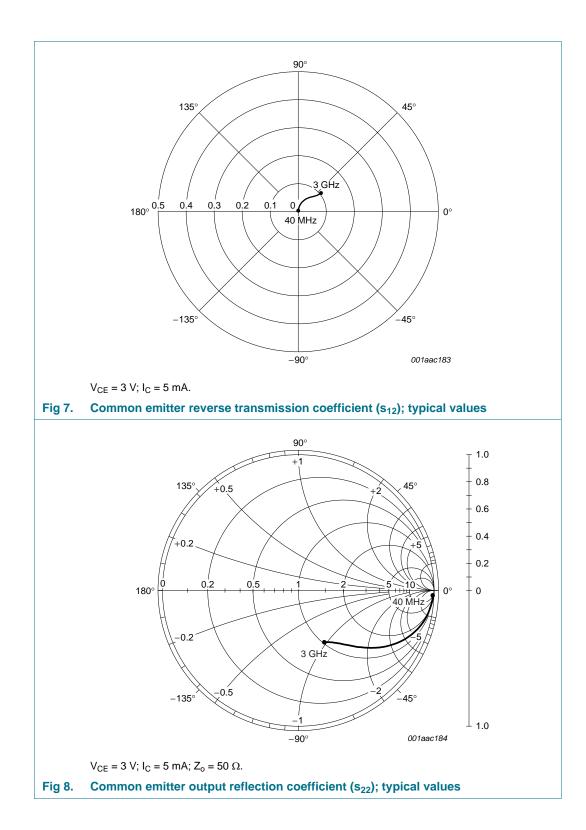
### NPN 14 GHz wideband transistor



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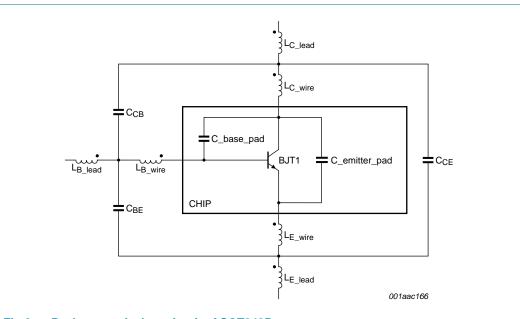
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## 8. Application information

Table 8. S	PICE parameters of the BF	G310W DIE	
Sequence	Parameter	Value	Unit
1	IS	16.17	aA
2	BF	210	-
3	NF	1	-
4	VAF	50	V
5	IKF	59.83	mA
6	ISE	1.726	fA
7	NE	2.114	-
8	BR	6	-
9	NR	1	-
10	VAR	2.3	V
11	IKR	10	Α
12	ISC	0	aA
13	NC	1.5	-
14	RB	3.6	Ω
15	RE	2.1	Ω
16	RC	1.6	Ω
17	CJE	115.6	fF
18	VJE	866.3	mV
19	MJE	0.285	-
20	CJC	68.18	fF
21	VJC	601	mV
22	MJC	0.123	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.3	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	°C
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	1	-
		· ·	

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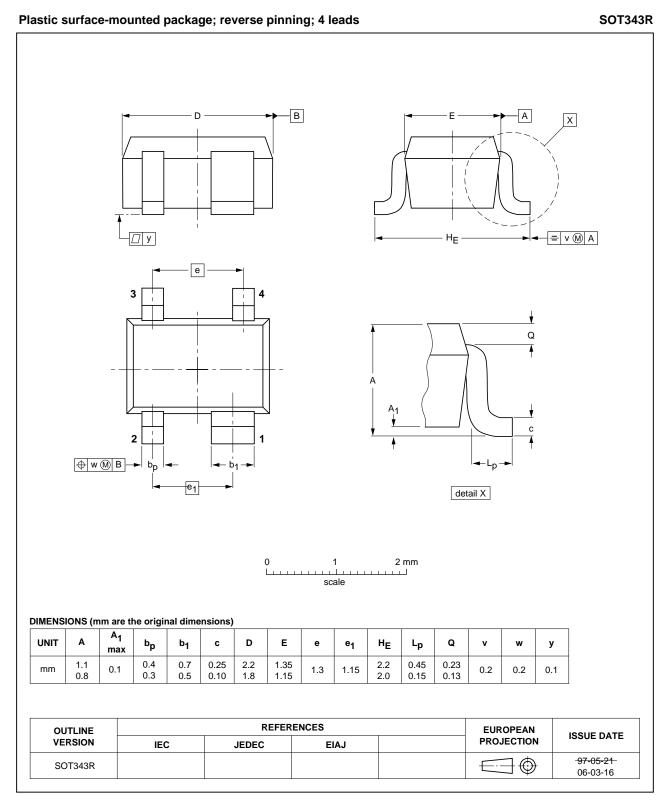
### Fig 9. Package equivalent circuit of SOT343R

#### Table 9. List of components; see Figure 9

Table 9. List of components, s	rigure 9	
Designation	Value	Unit
C <sub>CB</sub>	2	fF
C <sub>BE</sub>	80	fF
C <sub>CE</sub>	80	fF
C_base_pad	67	fF
C_emitter_pad	142	fF
L <sub>C_wire</sub>	0.767	nH
L <sub>B_wire</sub>	0.842	nH
L <sub>E_wire</sub>	0.212	nH
L <sub>C_lead</sub>	0.28	nH
L <sub>B_lead</sub>	0.281	nH
L <sub>E_lead</sub>	0.1	nH

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### 9. Package outline



### Fig 10. Package outline SOT343R

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BFG310W\_XR

## **10. Revision history**

Table 10. Revision his	tory					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BFG310W_XR v.2	20110915	Product data sheet	-	BFG310W_XR v.1		
Modifications:		of this data sheet has beer of NXP Semiconductors.	n redesigned to comply w	vith the new identity		
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li>Package ou</li> </ul>	Itline drawings have been u	updated to the latest vers	ion.		
BFG310W_XR v.1 (9397 750 14245)	20050202	Product data sheet	-	-		

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### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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